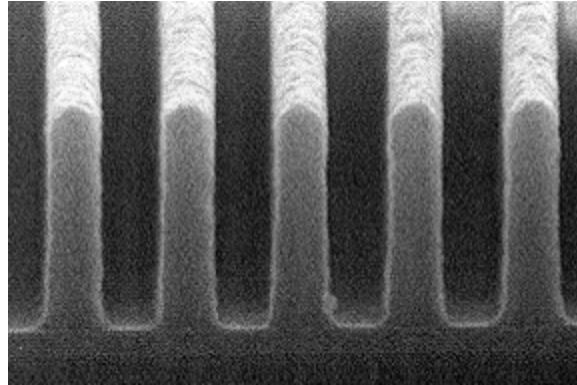


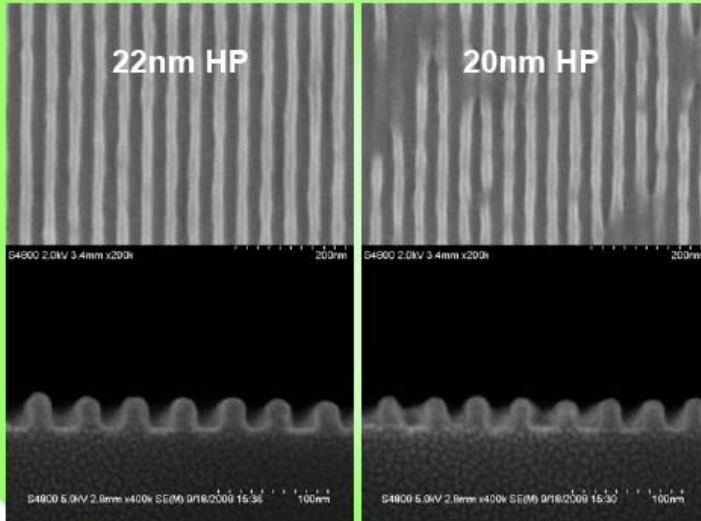
Skin (top) and T-top profile (bottom) in developed positive images due to airborne base contamination



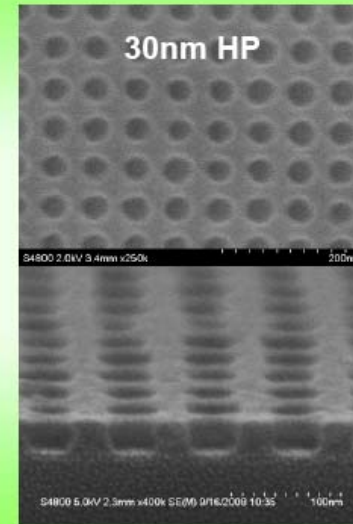
ESCAP (Environmentally Stable Chemical Amplification Positive resist) based on annealing concept to prevent airborne base diffusion: 125 nm equal line/space patterns printed at 248 nm (KrF excimer laser)

July 2008

2008



EUV
CAR



Very small features (22-20 nm equal line/space patterns and 30 nm contact holes) printed in a chemical amplification resist (CAR) by EUV (extreme ultraviolet, 13.4 nm) at SEMATECH